

Small Signal Schottky Diode



LINKS TO ADDITIONAL RESOURCES



MECHANICAL DATA

Case: MiniMELF (SOD-80)

Weight: approx. 31 mg

Cathode band color: black

Packaging codes/options:

GS18/10K per 13" reel (8 mm tape), 10K/box

GS08/2.5K per 7" reel (8 mm tape), 12.5K/box

FEATURES

- For general purpose applications
- The LL101 series is a metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring
- The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications
- Integrated protection ring against static discharge
- Low capacitance
- Low leakage current
- This diode is also available in the DO-35 (DO-204AH) case with type designation SD101A, SD101B, SD101C and in the SOD-123 case with type designation SD101AW, SD101BW, SD101CW
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT

APPLICATIONS

- HF-detector
- Protection circuit
- Diode for low currents with a low supply voltage
- Small battery charger
- Power supplies
- DC/DC converter for notebooks

PARTS TABLE

PART	TYPE DIFFERENTIATION	ORDERING CODE	CIRCUIT CONFIGURATION	REMARKS
LL101A	$V_R = 60\text{ V}$, V_F at $I_F = 1\text{ mA}$ max. 410 mV	LL101A-GS18 or LL101A-GS08	Single	Tape and reel
LL101B	$V_R = 50\text{ V}$, V_F at $I_F = 1\text{ mA}$ max. 400 mV	LL101B-GS18 or LL101B-GS08	Single	Tape and reel
LL101C	$V_R = 40\text{ V}$, V_F at $I_F = 1\text{ mA}$ max. 390 mV	LL101C-GS18 or LL101C-GS08	Single	Tape and reel

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	PART	SYMBOL	VALUE	UNIT
Reverse voltage		LL101A	V_{RRM}	60	V
		LL101B	V_{RRM}	50	V
		LL101C	V_{RRM}	40	V
Power dissipation (infinite heatsink) ⁽¹⁾			P_{tot}	400	mW
Forward continuous current			I_F	30	mA
Maximum single cycle surge 10 μs square wave			I_{FSM}	2	A

Note

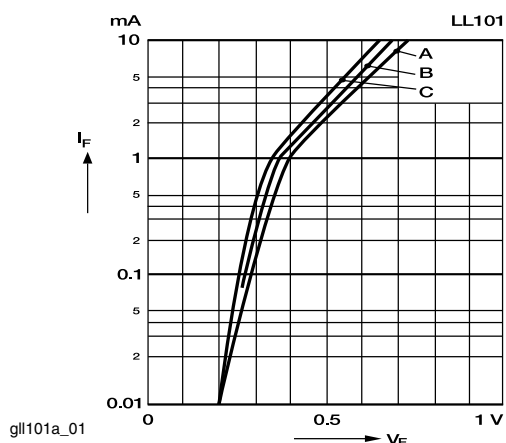
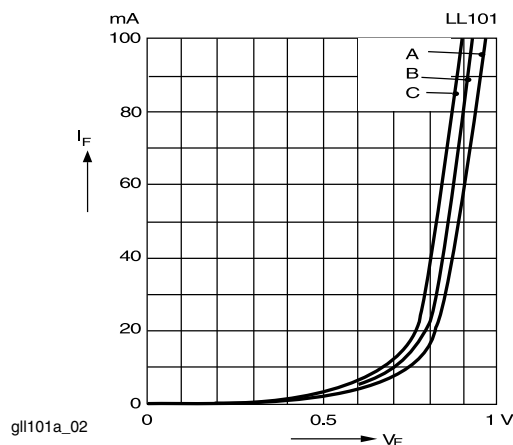
⁽¹⁾ Valid provided that electrodes are kept at ambient temperature

THERMAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Junction temperature		T_j	125	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal resistance junction to ambient air	On PC board 50 mm x 50 mm x 1.6 mm	R_{thJA}	320	K/W

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Reverse Breakdown Voltage	$I_R = 10\text{ }\mu\text{A}$	LL101A	$V_{(BR)}$	60			V
		LL101B	$V_{(BR)}$	50			V
		LL101C	$V_{(BR)}$	40			V
Leakage current	$V_R = 50\text{ V}$	LL101A	I_R			200	nA
	$V_R = 40\text{ V}$	LL101B	I_R			200	nA
	$V_R = 30\text{ V}$	LL101C	I_R			200	nA
Forward voltage drop	$I_F = 1\text{ mA}$	LL101A	V_F			0.410	V
	$I_F = 1\text{ mA}$	LL101B	V_F			0.400	V
	$I_F = 1\text{ mA}$	LL101C	V_F			0.390	V
	$I_F = 15\text{ mA}$	LL101A	V_F			1000	mV
		LL101B	V_F			950	mV
		LL101C	V_F			900	mV
Diode capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$	LL101A	C_D			2.0	pF
	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$	LL101B	C_D			2.1	pF
		LL101C	C_D			2.2	pF
Reverse recovery time	$I_F = I_R = 5\text{ mA}$, recover to $0.1\text{ }I_R$		t_{rr}			1	ns

TYPICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Fig. 1 - Typ. I_F vs. V_F for Primary Conduction through the Schottky Barrier

Fig. 2 - Typ. I_F of Combination Schottky Barrier and PN Junction Guard Ring

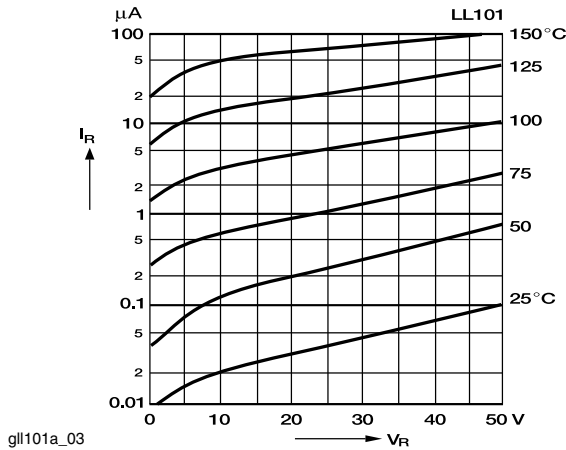


Fig. 3 - Typical Variation of Reverse Current at Various Temperatures

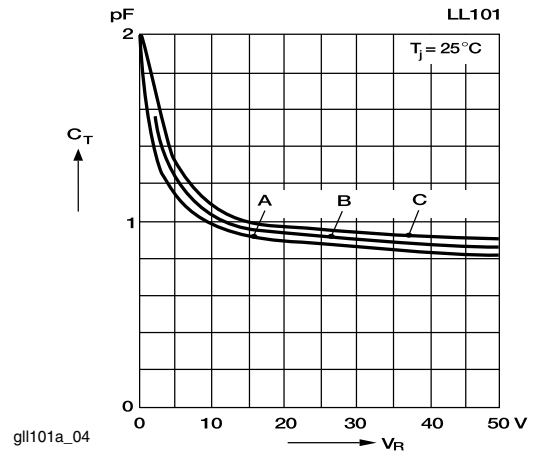
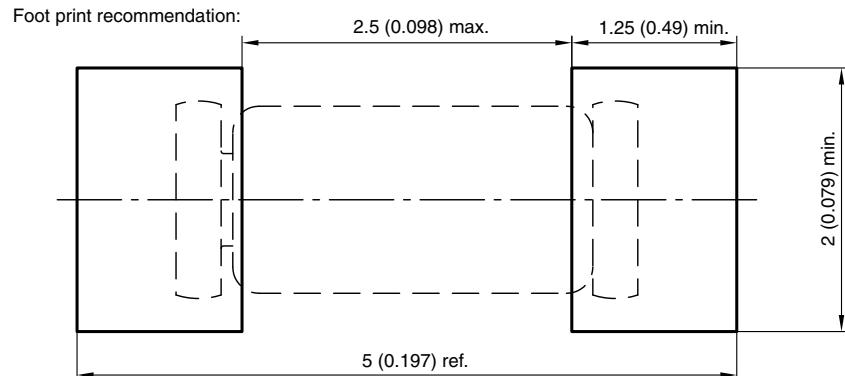
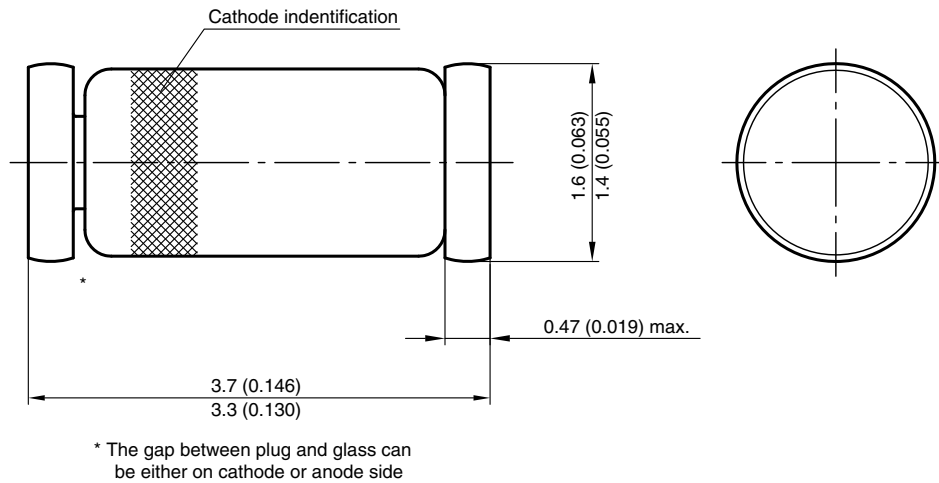


Fig. 4 - Typical Capacitance Curve as a Function of Reverse Voltage

PACKAGE DIMENSIONS in millimeters (inches): **MiniMELF (SOD-80)**



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